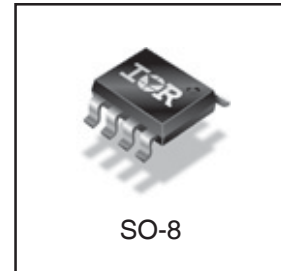
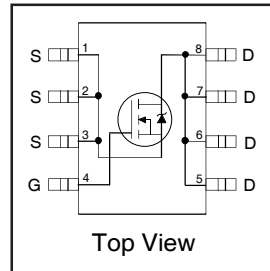


HEXFET® Power MOSFET

V_{DS}	30	V
$R_{DS(on) \max}$ (@ $V_{GS} = 10V$)	4.8	m Ω
Q_g (typical)	17	nC
I_D (@ $T_A = 25^\circ C$)	18	A



Applications

- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for Isolated DC-DC Converters in Networking Systems

Features

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification

⇒

Benefits

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF8736PbF-1	SO-8	Tube/Bulk	95	IRF8736PbF-1
		Tape and Reel	4000	IRF8736TRPbF-1

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	18	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	14.4	
I_{DM}	Pulsed Drain Current ①	144	
P_D @ $T_A = 25^\circ C$	Power Dissipation ④	2.5	W
P_D @ $T_A = 70^\circ C$	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④⑤	—	50	

Notes ① through ⑤ are on page 9

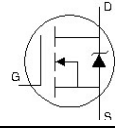
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

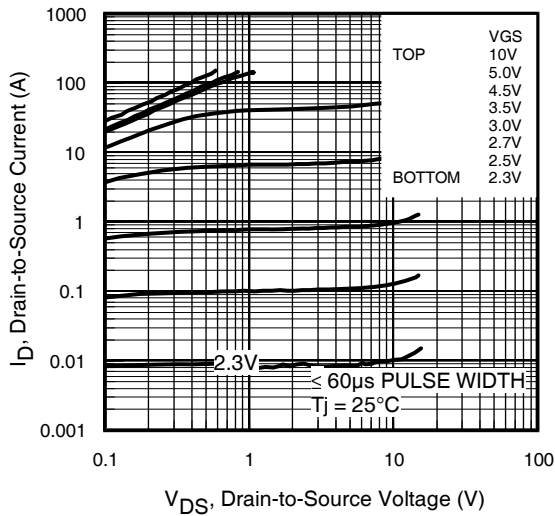
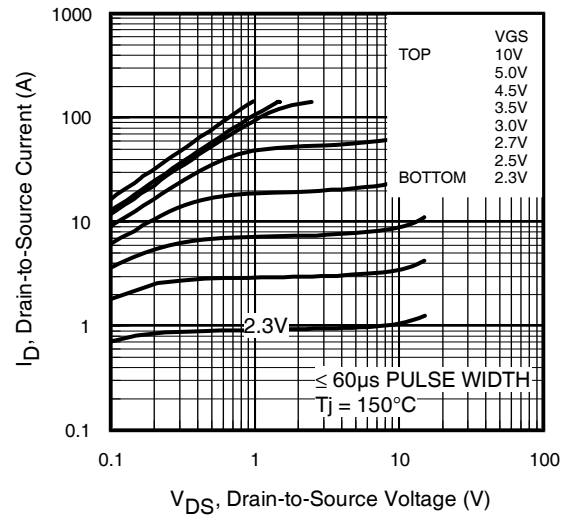
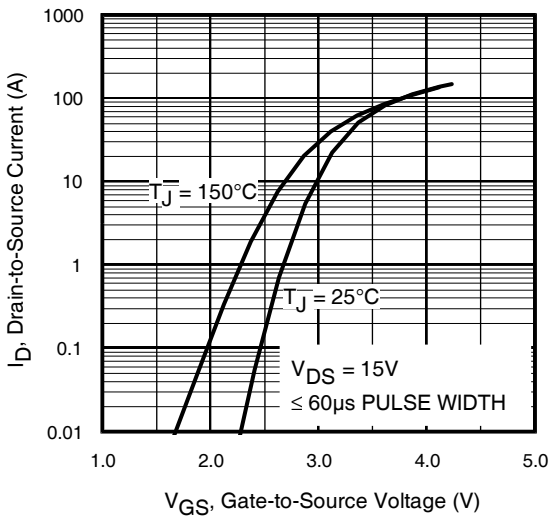
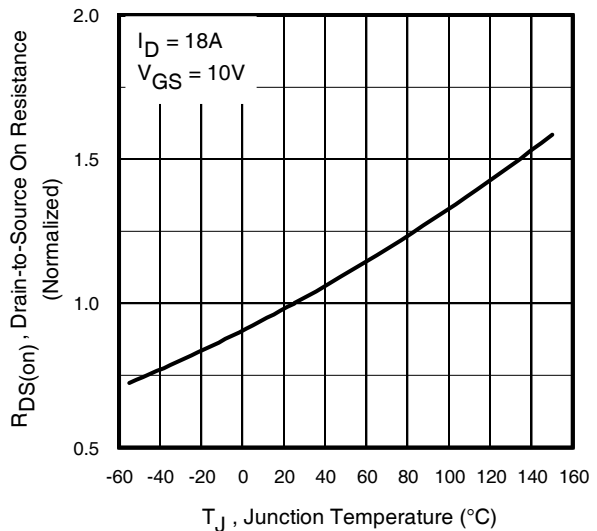
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.9	4.8	$\text{m}\Omega$	$V_{GS} = 10V, I_D = 18A$ ③
		—	5.5	6.8		$V_{GS} = 4.5V, I_D = 14.4A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	$V_{DS} = V_{GS}, I_D = 50\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.1	—	$\text{mV}/^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	52	—	—	S	$V_{DS} = 15V, I_D = 14.4A$
Q_g	Total Gate Charge	—	17	26	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 14.4A$ See Fig. 16
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	4.4	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.9	—		
Q_{gd}	Gate-to-Drain Charge	—	5.8	—		
Q_{godr}	Gate Charge Overdrive	—	4.9	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	7.7	—		
Q_{oss}	Output Charge	—	7.1	—	nC	$V_{DS} = 10V, V_{GS} = 0V$
R_G	Gate Resistance	—	1.3	2.2	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 14.4A$ $R_G = 1.8\Omega$ See Fig. 14
t_r	Rise Time	—	15	—		
$t_{d(off)}$	Turn-Off Delay Time	—	13	—		
t_f	Fall Time	—	7.5	—		
C_{iss}	Input Capacitance	—	2315	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	449	—		
C_{rss}	Reverse Transfer Capacitance	—	219	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	126	mJ
I_{AR}	Avalanche Current ①	—	14.4	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	144		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 14.4A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	16	24	ns	$T_J = 25^\circ\text{C}, I_F = 14.4A, V_{DD} = 10V$
Q_{rr}	Reverse Recovery Charge	—	19	29	nC	$di/dt = 300A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

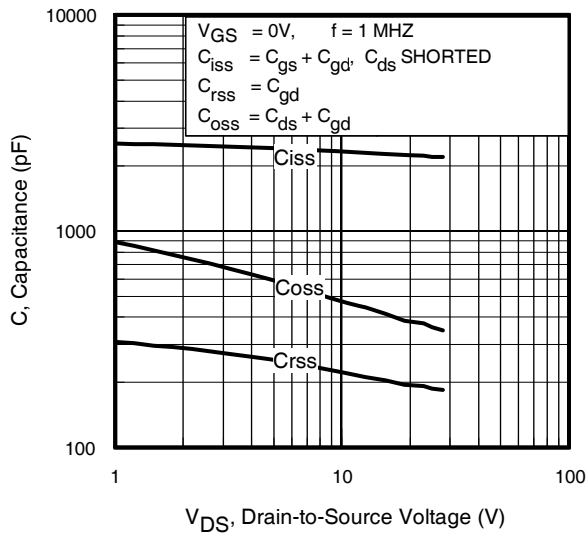


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

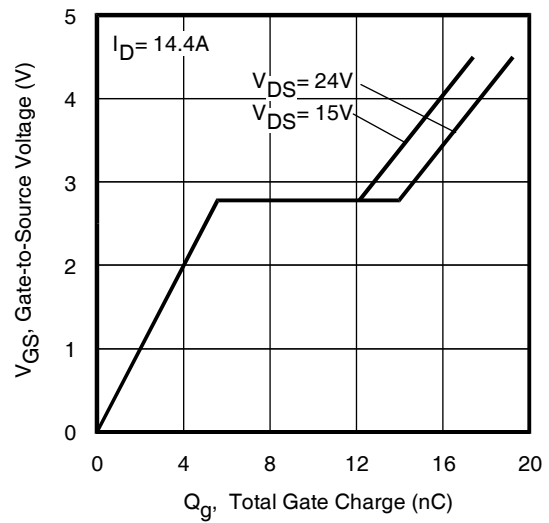


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

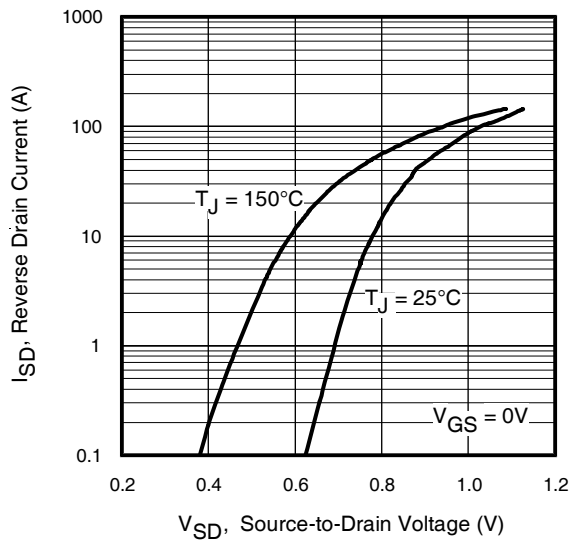


Fig 7. Typical Source-Drain Diode Forward Voltage

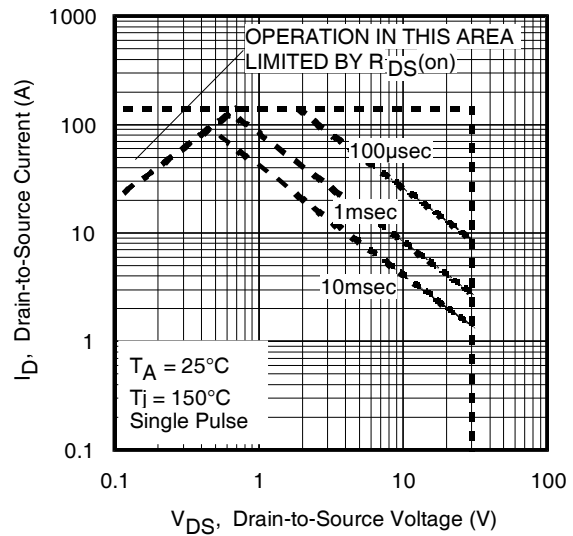


Fig 8. Maximum Safe Operating Area

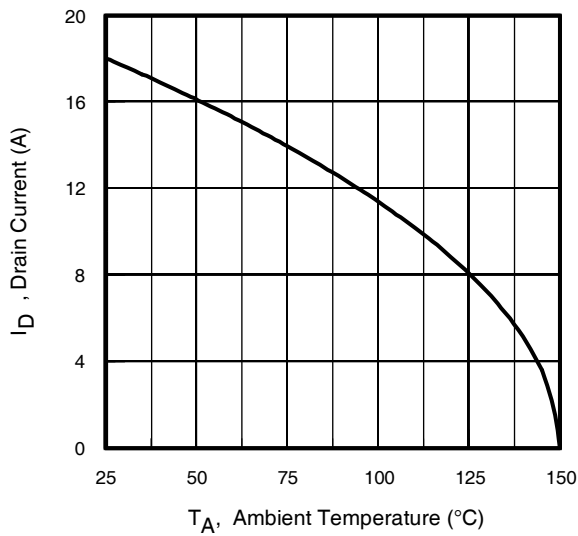


Fig 9. Maximum Drain Current Vs. Ambient Temperature

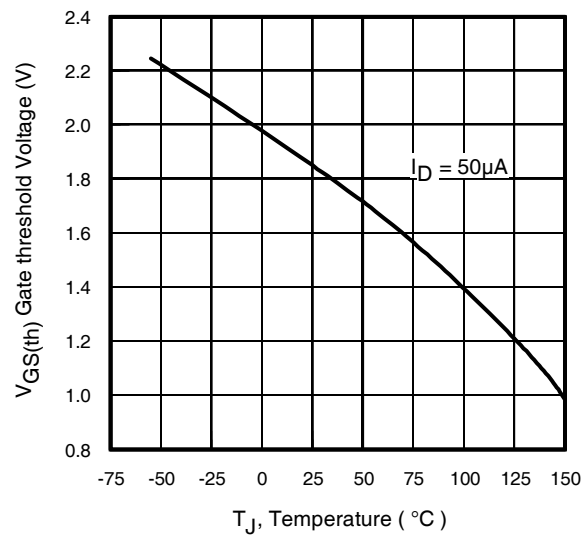


Fig 10. Threshold Voltage Vs. Temperature

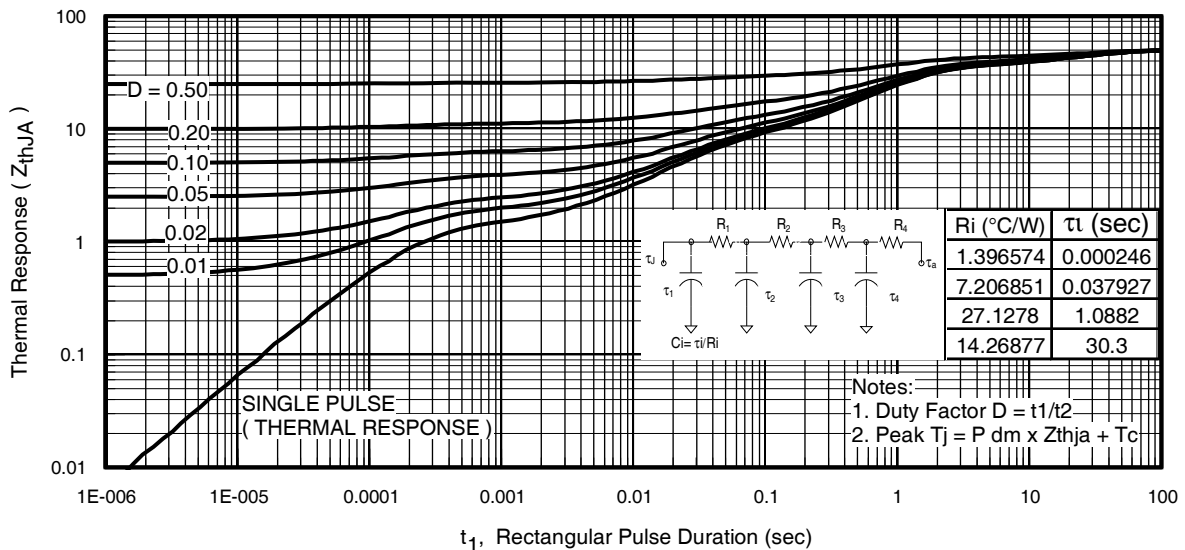
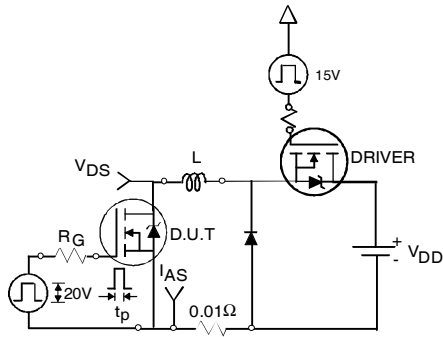
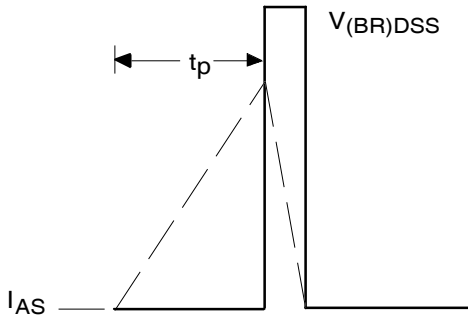
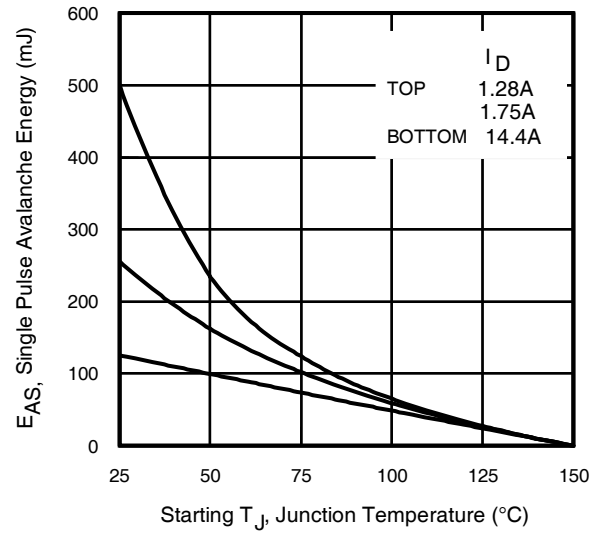
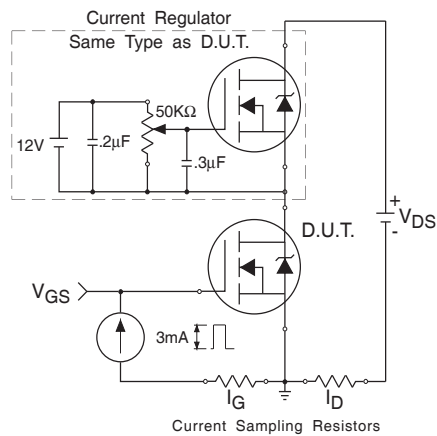
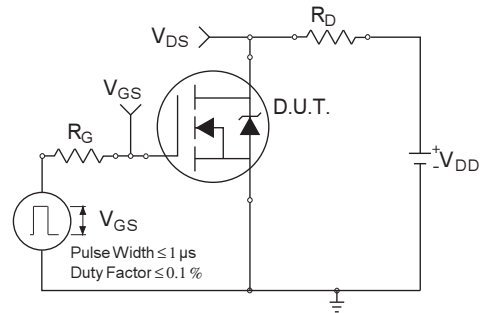
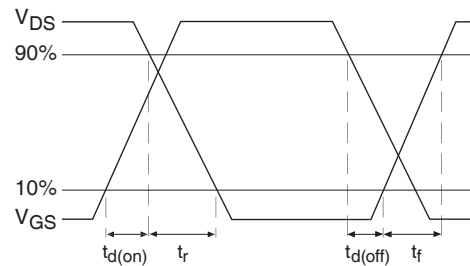


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12a. Unclamped Inductive Test Circuit

Fig 12b. Unclamped Inductive Waveforms

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Fig 13. Gate Charge Test Circuit

Fig 14a. Switching Time Test Circuit

Fig 14b. Switching Time Waveforms

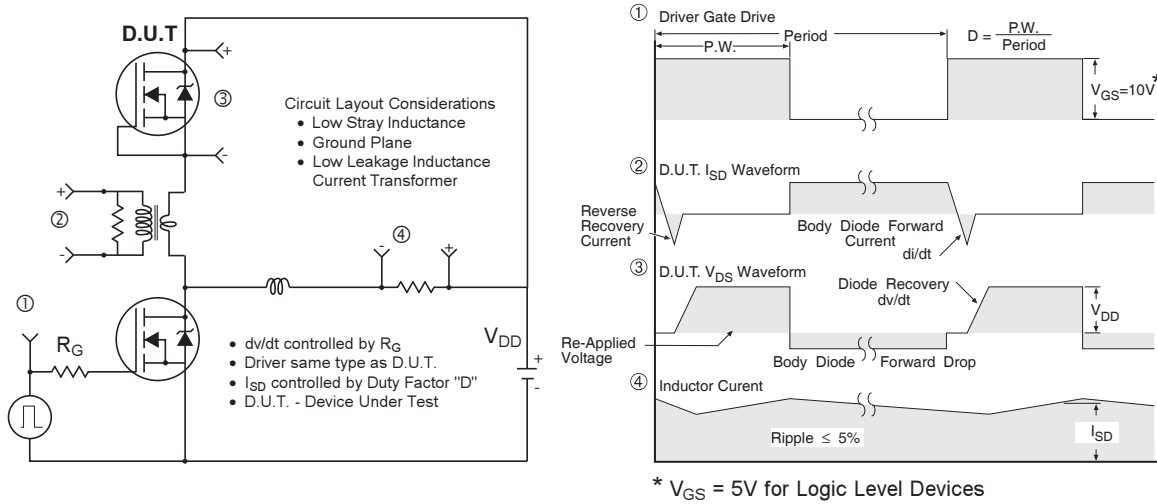


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

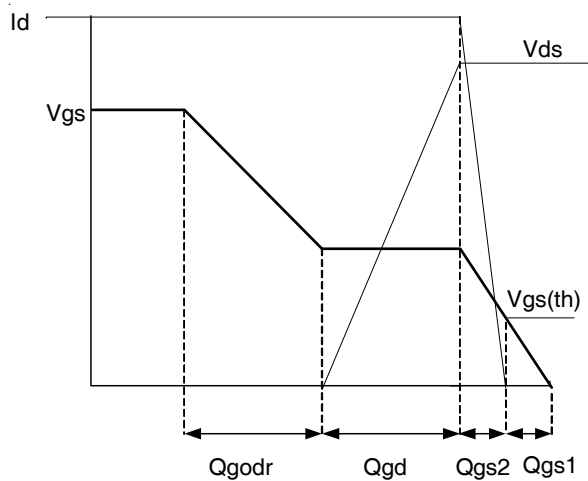
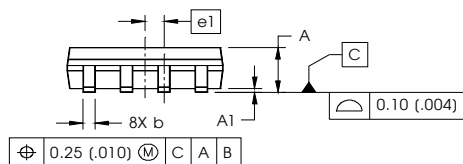
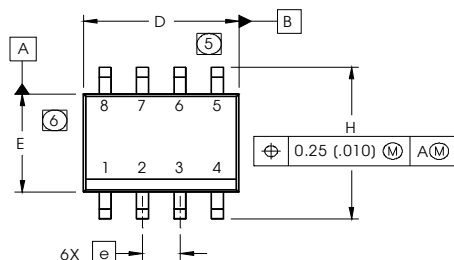


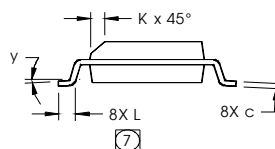
Fig 16. Gate Charge Waveform

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



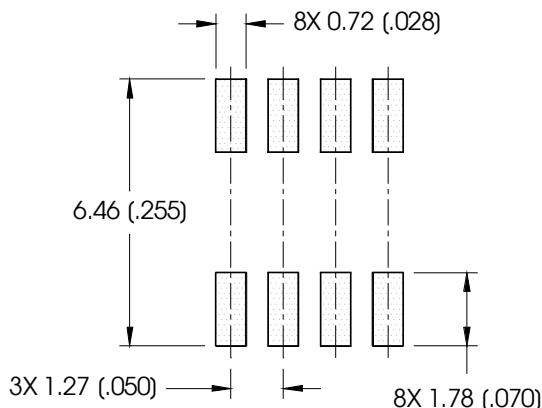
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
γ	0°	8°	0°	8°



FOOTPRINT

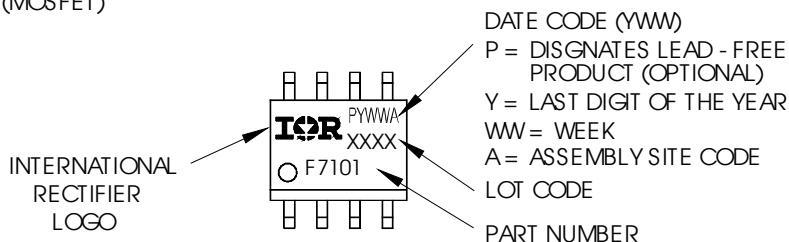
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

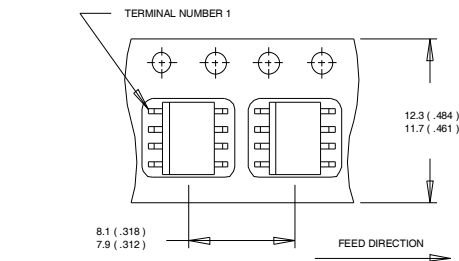


SO-8 Part Marking Information

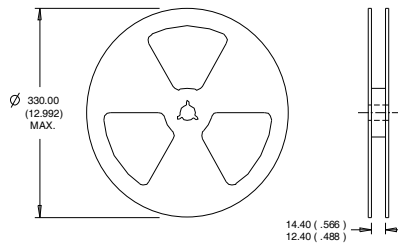
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))


NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industrial (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 1.21\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 14.4\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board
- ⑤ R_{θ} is measured at T_J approximately 90°C

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>